TP $\mathbf{5}^{\text{ème}}$ semestre Electricité, $\mathbf{6}^{\text{ème}}$ semestre Microtechnique

Composants à disposition

Composants discrets

Si small signal diode, $I_{F,max} = 150 \text{ mA}$, $V_{R,max} = 75 \text{ V}$, $t_{rr,max} = 8 \text{ ns}$
Si small signal diode, $I_{F,max} = 250 \text{ mA}$, $V_{R,max} = 75 \text{ V}$, $t_{rr,max} = 4 \text{ ns}$
Si IR photodiode, $\lambda_{peak} = 950 \text{ nm}$, $I_{ra} = 45 \mu A$ at $E_e = 1 \text{ mW/cm}^2$
GaAs IR LED, $\lambda_{\text{peak}} = 950 \text{ nm}$, $I_{\text{e,typ}} = 120 \text{ mW/sr}$
Red or Green LED, $I_{F,typ} = 20 \text{ mA}$
NPN, small signal, $I_{C,max} = 100 \text{ mA}$, $V_{CE,max} = 45 \text{ V}$, $P_{max} = 300 \text{ mW}$, $\beta_{typ} = 300 \text{ mW}$
NPN, small signal, $I_{C,max} = 100 \text{ mA}$, $V_{CE,max} = 20 \text{ V}$, $P_{max} = 300 \text{ mW}$, $\beta_{typ} = 500 \text{ mW}$
PNP, small signal, $I_{C,max} = 100 \text{ mA}$, $V_{EC,max} = 45 \text{ V}$, $P_{max} = 300 \text{ mW}$, $\beta_{typ} = 300 \text{ mW}$
NPN switching, $I_{C,max} = 800 \text{mA}$, $V_{CE,max} = 30 \text{V}$, $P_{max} = 600 \text{mW}$
PNP switching, $I_{C,max} = 600 \text{ mA}$, $V_{EC,max} = 40 \text{ V}$, $P_{max} = 600 \text{ mW}$
NPN power, $I_{C,max} = 3 \text{ A}$, $V_{CE,max} = 45 \text{ V}$, $P_{max} = 40 \text{ W}$
PNP power, $I_{C,max} = 3 \text{ A}$, $V_{EC,max} = 45 \text{ V}$, $P_{max} = 40 \text{ W}$
NPN power darlington, $I_{C,max} = 5 \text{ A}$, $V_{CE,max} = 60 \text{ V}$, $P_{max} = 65 \text{ W}$, $\beta_{min} = 1000$
PNP power darlington, $I_{C,max} = 5 \text{ A}$, $V_{EC,max} = 60 \text{ V}$, $P_{max} = 65 \text{ W}$, $\beta_{min} = 1000$
NMOS power, logic level gate drive, $R_{DS,ON} = 0.28 \Omega$ at $V_{GS} = 4 V$
NMOS power, logic level gate drive, $R_{DS,ON} = 11 \text{ m}\Omega$ at $V_{GS} = 4.5 \text{ V}$
NMOS power, $V_{DS,max} = 55 \text{ V}$, $I_{D,max} = 17 \text{ A}$, $R_{DS,ON} = 70 \text{ m}\Omega$ at $V_{GS} = 10 \text{ V}$
PMOS power, $V_{SD,max} = 60 \text{ V}$, $I_{D,max} = 11 \text{ A}$, $R_{DS,ON} = 0.28 \Omega$ at $V_{GS} = 10 \text{ V}$

Amplificateurs opérationnels

UA741	general purpouse, bipolar, GBW = 1 MHz, $SR = 1 \text{ V/}\mu\text{s}$
TL071	FET input, general purpouse, bipolar, $GBW = 4 MHz$, $SR = 13 V/\mu s$
TL072	dual, FET input, general purpouse, bipolar, $GBW = 4 \text{ MHz}$, $SR = 13 \text{ V/}\mu\text{s}$
LF356	FET input, general purpouse, bipolar, $GBW = 5 \text{ MHz}$, $SR = 12 \text{ V/}\mu\text{s}$
LM318	fast, bipolar, GBW = 15 MHz , SR = $50 \text{ V/}\mu\text{s}$
LM358	dual, bipolar, $V_{\text{supply,total}} = 3$ to 30 V , $V_{\text{in, common-mode,min}} = V_{-}$, $GBW = 1 \text{ MHz}$
LMC662	dual, CMOS, Rail-to-Rail Output, $V_{supply,total}$ = 5 to 15 V, $V_{in,common-mode,min}$ = V GBW = 1.1 MHz, SR = 1 V/ μs
MC6482	dual, CMOS, Rail-to-Rail Input and Output, $V_{supply,total}=3$ to 16 V, GBW = 1.5 MHz, SR = 1.3 V/ μs
MCP6292	dual, CMOS, Rail-to-Rail Input and Output, $V_{\text{supply,total}} = 2.4$ to 6 V, GBW = 10 MHz, SR = 7 V/ μ s

EPF- LAUSANNE SECTION GENIE ELECTRIQUE ET ELECTRONIQUE

Comparateurs

LM311 general purpouse, bipolar, $V_{\text{supply,total}} = 3.5 \text{ to } 30 \text{ V}$, $t_{\text{response}} < 200 \text{ ns}$

open Collector or open Emitter output.

LM393 dual, low power, bipolar, $V_{\text{supply,total}} = 2 \text{ to } 36 \text{ V}$, $t_{\text{response}} = 1.3 \,\mu\text{s}$

 $V_{\text{in. common-mode.min}} = V_{-}$, open Collector output.

IC analogiques divers

NE555 précision timer, bipolar, V_{supply,total} = 4.5 to 16 V

TLC555 CMOS 555 timer, low power, $V_{\text{supply,total}} = 2 \text{ to } 15 \text{ V}$

CA3046 NPN array

LM2917N F to V converter

7805 Voltage regulator, 5 V 1 A TC1426 MOS gate driver, inverting

TC1427 MOS gate driver, non-inverting

Logique CMOS 4000

HEF4001 quadruple 2-input NOR

HEF4007 dual CMOS pair + one inverter

HEF4011 quadruple 2-input NAND

HEF4012 dual 4-input NAND

HEF4013 dual D flip-flop

HEF4017 by 10 Johnson counter, decoded output

HEF4022 by 8 Johnson counter, decoded output

HEF4027 dual JK flip-flop

HEF4040 12 stage binary counter

HEF4046 PLL

HEF4049 hex inverting buffer

HEF4050 hex non-inverting buffer

HEF4068 8-input NAND

HEF4069 hex inverter, (suffix U = non-buffered)

HEF4070 quadruple XOR

HEF4071 quadruple 2-input OR HEF4081 quadruple 2-input AND

HEF4093 quadruple 2-input NAND with Schmitt trigger

HEF40106 hex inverter with Schmitt trigger

HEF4516 4-bit binary up/down counter

HEF4518 dual BCD counter

HEF4520 dual 4-bit binary counter

HEF4526 programmable 4-bit binary down counter

HEF4538 dual monostable